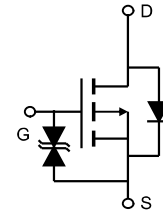


Description

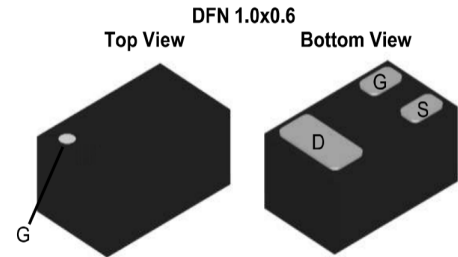
The AP1605 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch



Schematic diagram

Features

- $V_{DS} = -20V, I_D = -0.7A$
 $R_{DS(ON)} < 420m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)} < 500m\Omega$ @ $V_{GS} = -2.5V$
- Lead free product is acquired
- Surface mount package



Application

- Load switch

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
1605	AP1605	DFN1006	-	-	10000

Symbol	Parameter		Rating	Unit
Common Ratings (T _c =25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage		±8	V
V _{(BR)DSS}	Drain-Source Breakdown Voltage		-20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	-0.7	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	T _C =25°C	-2	A
I _D	Continuous Drain Current	T _C =25°C	-0.7	A
		T _C =100°C	-0.5	
P _D	Maximum Power Dissipation	T _C =25°C	0.9	W
R _{θJA}	Thermal Resistance Junction-Ambient		80	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current (T _c =25°C)	V _{DS} =-20V,V _{GS} =0V	--	--	-1	μA
	Zero Gate Voltage Drain Current (T _c =125°C)	V _{DS} =-20V,V _{GS} =0V	--	--	-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±8 V,V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =-250μA	-0.45	-0.6	-1.0	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-4.5V,I _D =-0.5A	--	360	420	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-2.5V,I _D =-0.3A	--	400	500	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-10V,V _{GS} =0V, f=1MHz	--	50	--	pF
C _{oss}	Output Capacitance		--	12	--	pF
C _{rss}	Reverse Transfer Capacitance		--	6.5	--	pF
Q _g	Total Gate Charge	V _{DS} =-10V,I _D =-0.4A, V _{GS} =-4.5V	--	0.8	--	nC
Q _{gs}	Gate-Source Charge		--	0.15	--	nC
Q _{gd}	Gate-Drain Charge		--	0.2	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, R _G =3Ω, V _{GS} =-4.5V, R _L =25Ω,	--	6	--	nS
t _r	Turn-on Rise Time		--	5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	23	--	nS
t _f	Turn-Off Fall Time		--	8	--	nS
Source- Drain Diode Characteristics						
I _{SD}	Source-drain current(Body Diode)	T _c =25°C	--	--	-0.7	A
I _{SDM}	Pulsed Source-drain current (Body Diode)		--	--	-3	A
V _{SD}	Forward on voltage	T _J =25°C,I _{SD} =- 0.5A, V _{GS} =0V	--	--	-1.2	V

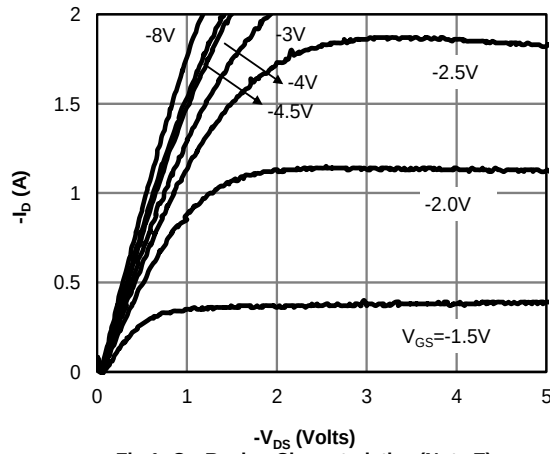


Fig 1: On-Region Characteristics (Note E)

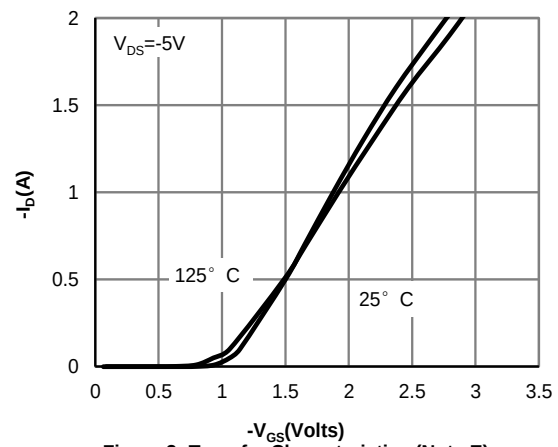


Figure 2: Transfer Characteristics (Note E)

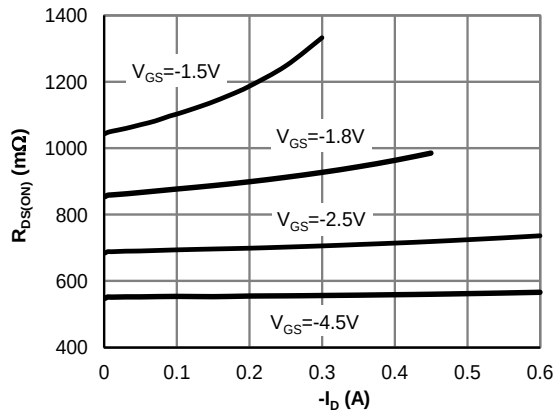


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

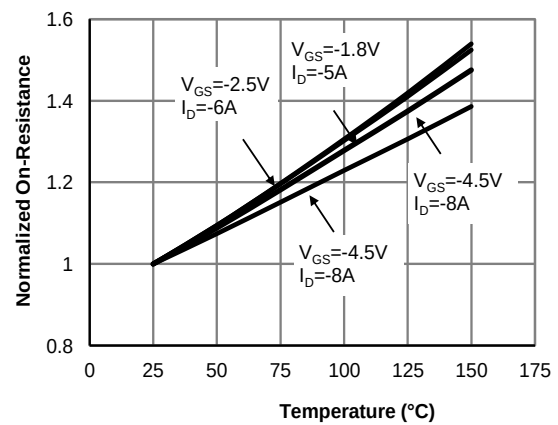


Figure 4: On-Resistance vs. Junction Temperature (Note E)

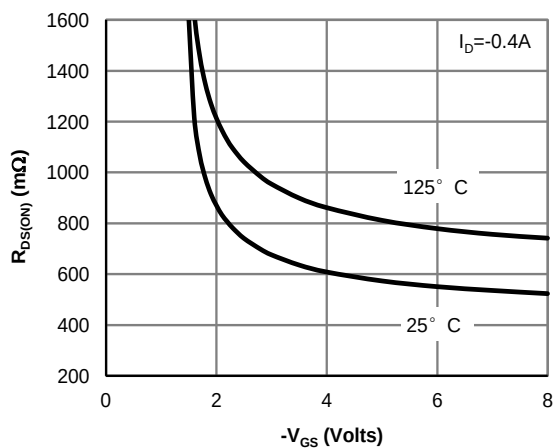


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

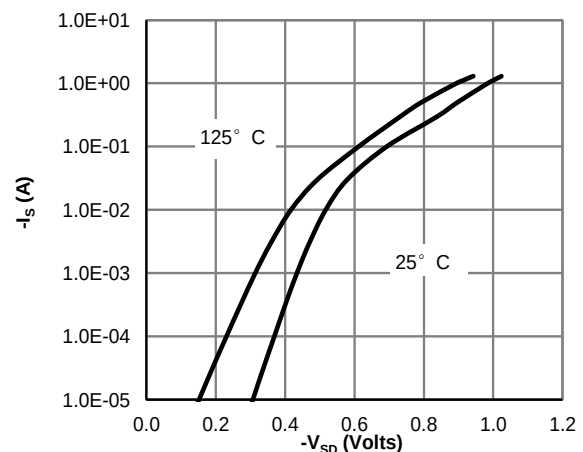


Figure 6: Body-Diode Characteristics (Note E)

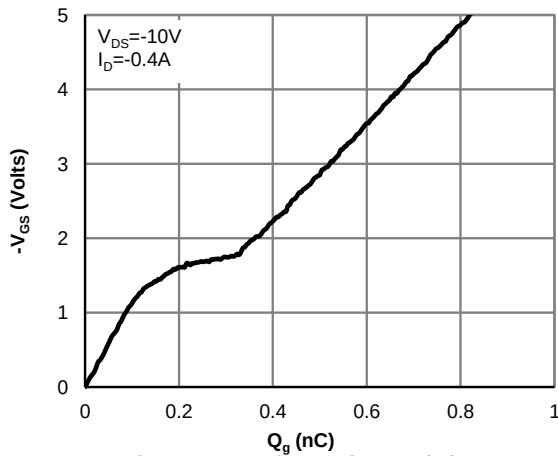


Figure 7: Gate-Charge Characteristics

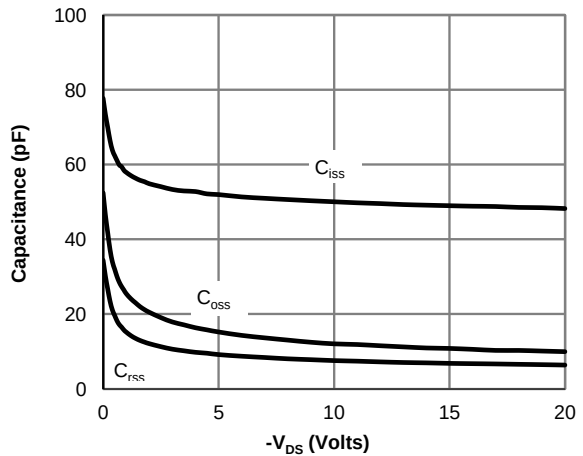


Figure 8: Capacitance Characteristics

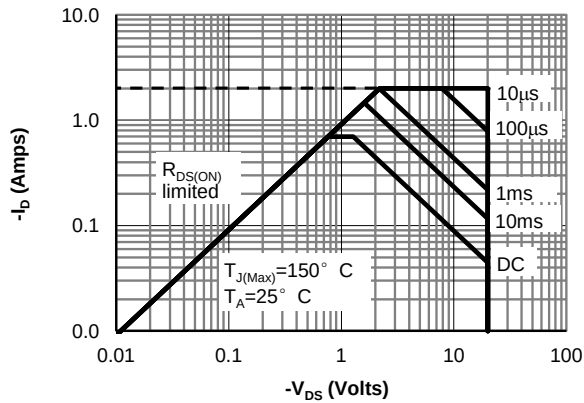


Figure 9: Maximum Forward Biased Safe Operating Area (Note B)

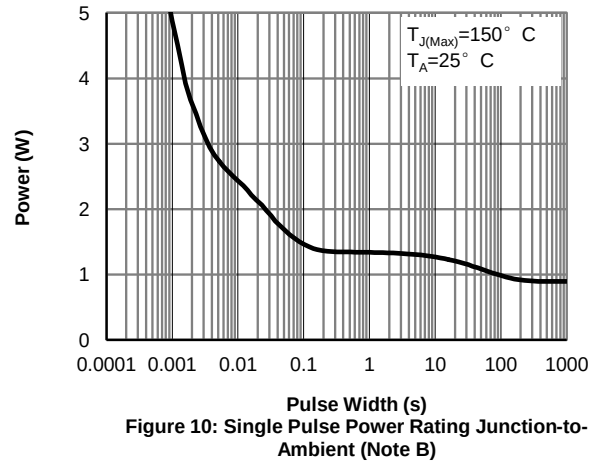


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note B)

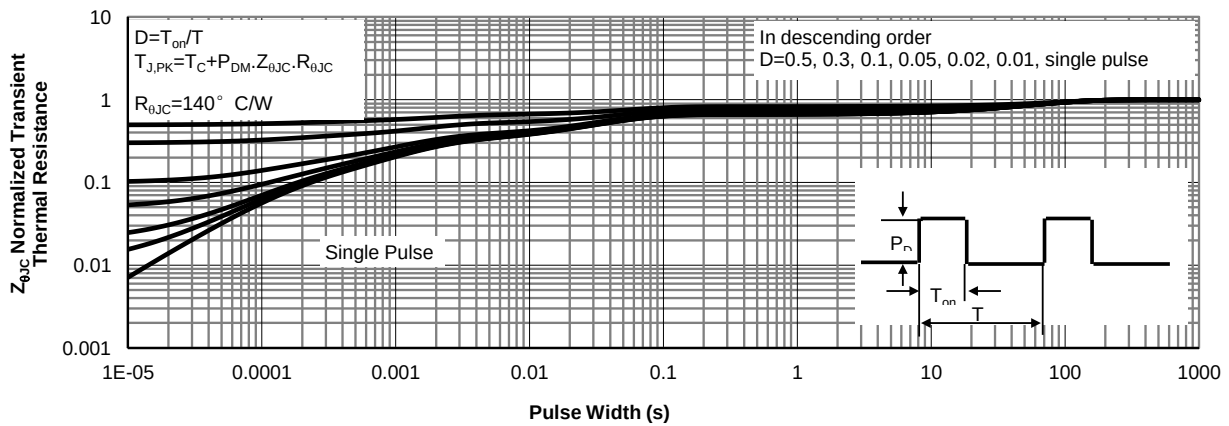
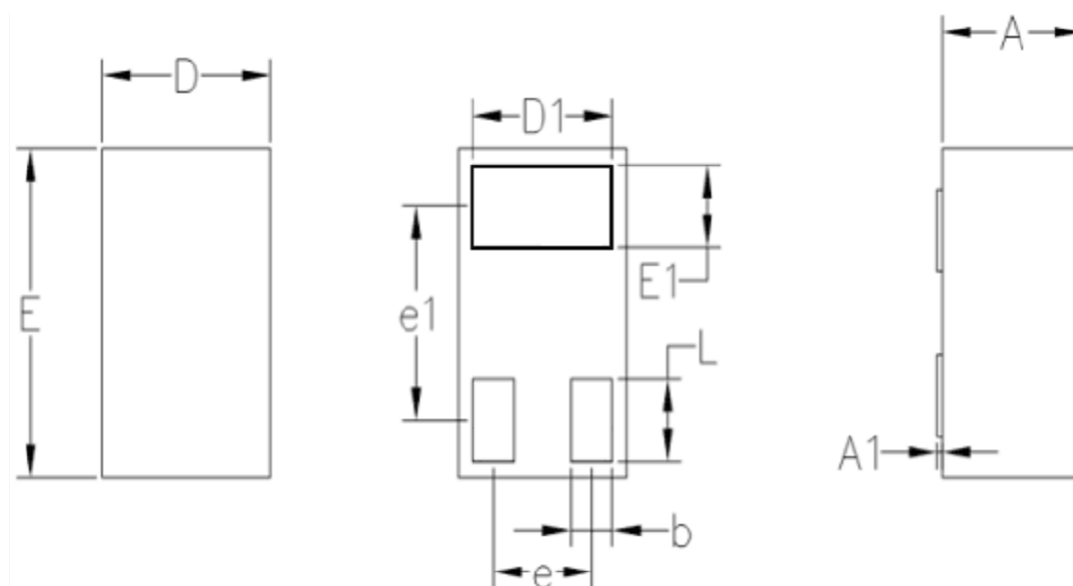


Figure 11: Normalized Maximum Transient Thermal Impedance (Note B)

Package Dimensions
DFN1006



SYMBOL	DIMENSIONS IN MM		
	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0.00	—	0.05
D	0.55	0.60	0.65
E	0.95	1.00	1.05
D1	0.45	0.50	0.55
E1	0.20	0.25	0.30
L	0.20	0.25	0.30
b	0.10	0.15	0.20
e	0.35BSC		
e1	0.65BSC		